

	U.S. PATENT DOCUMENTS									
Examiner Initials	Cite No. ¹	U.S. Patent Document	Kind Code if known ²	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD- YYYY	Pages, Columns Lines Where Relevant Passages or Relevant Figures Appear				
EK.		2001/0012702		KIM	08/09/2001					
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Cite No. 1	Foreign Patent Document Office ³ Number ⁴ Kind Code ⁵ (if known)	Country	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD- YYYY	Pages, Columns Lines Where Relevant Passages or Relevant Figures Appear			
	1999-0031801	KR	KIM	05/06/1999				
	1999-023628	KR	TOSHIBA CORP	03/25/1999	-			
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Other Prior Art-Non Patent Literature Documents

Other I	101 71	t-riou rateut Literatur	e Documents				
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), data, page(s), volume-issue number(s), publisher, country, where published, source. Applicant check her English language translation attached					
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Examiner: Initial if re	ference conside	red, whether or not citation is in conformance with MPEP	609. Draw a line through citation if not in conformance	and not considered. Include cop-	of this form with next communication to		

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Patent and Trademark Office U.S. DEPARTMENT OF COMMERCE Please type a plus sign $(+) \rightarrow +$ 1449/PTO

Kind Code

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Cited Document

Name of Patentee or Applicant of

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U.S. Patent Document

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

Sheet 1 of 2

Examiner

Initials

Cite No.1

Application No.	:	09/614,286
Filing Date	:	July12, 2000
First Named Inventor	:	Hiroshi Tanabe
Group Art Unit	:	2812
Examiner Name	-:	
Attorney Docket No.	:	NECK 17.552

Date of

Publication of

Cited Document

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ı	I	Patent and Trademark Office	Filing Date : July12, 2000	
ı	INFORMATI	ON DISCLOSURE	First Named Inventor: Hiroshi Tanabe	
١		I BY APPLICANT	Group Art Unit : 2812	
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ı	SHECK L UI L		Attorney Docket No · NECK 17,552	

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¹Unique citation designation number. ² See attached Kinds of U.S. Patent Documents. ³ Enter Office that Issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.1⁶ if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

Sheet 1 of 1

1449/PTO

Patent and Trademark Office U.S. DEPARTMENT OF COMMERCE Application No. : 09/614,286 Filing Date : July 12, 2000 First Named Inventor: Hiroshi Tanabe Group Art Unit 2812 **Examiner Name** Attorney Docket No. : NECK 17.552

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PIS		6-320292	JР	Nippon Steel Corp.	11/22/1994	

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